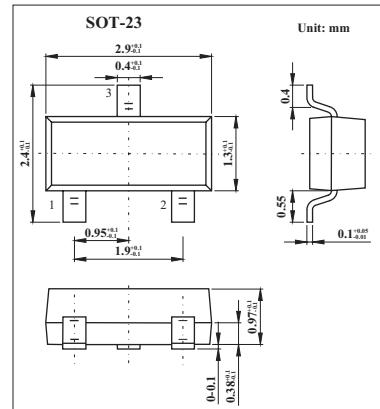


High-speed diode

BAS55

■ Features

- Small plastic SMD package
- High switching speed: max. 6ns
- Continuous reverse voltage: max. 60 V
- Repetitive peak forward current: max. 600 mA.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Repetitive peak reverse voltage	V _{RRM}			60	V
Continuous reverse voltage	V _R			60	V
Continuous forward current	I _F	Note 1		250	mA
Repetitive peak forward current	I _{FRM}			600	mA
Non-repetitive peak forward current	I _{FSM}	square wave; T _j = 25 °C prior to surge; t = 1 μ s t = 100 μ s t = 100 ms		9 3 1.7	A
Total power dissipation	P _{tot}	T _{mab} = 25 °C; Note 1		250	mW
Storage temperature	T _{stg}		-65	+150	°C
Junction temperature	T _j			150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode**BAS55****■ Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Conditions	Max	Unit
Forward voltage	V _F	I _F = 200 mA;DC value; Note 1	1.0	V
Reverse current	I _R	V _R = 60 V;	100	nA
		V _R = 60 V; T _j = 150 °C	100	μ A
Diode capacitance	C _d	f = 1 MHz; V _R = 0;	2.5	pF
Reverse recovery time	t _{rr}	when switched from I _F = 400 mA to I _R = 400 mA; R _L = 100 Ω ;measured at I _R = 40 mA;	6	ns
Forward recovery voltage	V _{f r}	when switched to I _F = 400 mA;t _r = 30 ns; when switched to I _F = 400 mA;t _r = 100 ns;	2 1.5	V

Note

1. Tamb = 25 °C; device has reached the thermal equilibrium when mounted on an FR4 printed-circuit board.

■ Marking

Marking	L5p
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